NSN 5962-00-163-6266

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View Online at https://aerobasegroup.com/nsn/5962-00-163-6266
Body Length:
Between 0.660 inches and 0.785 inches
Body Width:
Between 0.220 inches and 0.280 inches
Body Height:
Between 0.140 inches and 0.180 inches
Maximum Power Dissipation Rating:
450.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and monolithic and positive outputs and medium speed
Inclosure Material:
Ceramic and glass
Inclosure Configuration:
Dual-in-line Dual-in-line
Output Logic Form:
Current-mode logic
Input Circuit Pattern:
8 input
Case Outline Source And Designator:
T0-116 joint electron device engineering council
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
50.0 volts power source
Time Rating Per Chacteristic:
20.00 nanoseconds propagation delay time, low to high level output
Memory Device Type:
Diode matrix
Test Data Document:
82577-3255020 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
14 printed circuit
Shelf Life:
N/a
Unit Of Measure:

Demilitarization: Yes - demil/mli

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